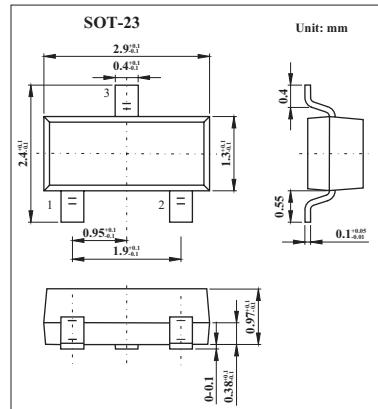


Silicon Schottky Barrier Diode

HRW0203A

■ Features

- Low forward voltage drop and suitable for high efficiency rectifying.
- MPAK package is suitable for high density surface mounting and high speed assembly.



■ Absolute Maximum Ratings Ta = 25°C

| Parameter | Symbol | Value | Unit |
|---|---------------------------|--------------|------|
| Repetitive peak reverse voltage | V _{RRM} | 20 | V |
| Average rectified current | I _o | 200 | mA |
| Non-repetitive peak forward surge current | I _{FSM} (Note 1) | 2 | A |
| Junction temperature | T _j | 125 | °C |
| Storage temperature | T _{stg} | -55 to + 125 | °C |

Note

1. 50 Hz sine wave 1 Pulse

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|-----------------|----------------|--------------------------------|-----|-----|------|------|
| Forward voltage | V _F | I _F = 200 mA | | | 0.50 | V |
| Reverse current | I _R | V _R = 30 V | | | 50 | µ A |
| Capacitance | C | V _R = 0 V, f = 1MHz | | 40 | | °C/W |

■ Marking

| | |
|---------|----|
| Marking | S5 |
|---------|----|